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Electrically tunable transport in the antiferromagnetic Mott insulator Sr$_2$IrO$_4$

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Electronic transport properties of the antiferromagnetic Mott insulator Sr$_2$IrO$_4$ have been investigated under extremely high electric biases. Using nanoscale contacts, we apply electric fields up to a few MV/m to a single crystal of Sr$_2$IrO$_4$ and observe a continuous reduction in the material’s resistivity with increasing bias, characterized by a reduction in the transport activation energy by as much as 16%. Temperature-dependent resistivity measurements provide a means to unambiguously retrieve the bias dependence of the activation energy from the Arrhenius plots at different biases. We further demonstrate the feasibility of reversible resistive switching induced by the electric bias, which is of interest for the emerging field of antiferromagnetic spintronics. Our findings demonstrate the potential of electrical means for tuning electronic properties in 5$d$ transition-metal oxides and suggest a promising path towards development of next-generation functional devices.

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I. INTRODUCTION

Electronic transport properties of conventional semiconductors, such as silicon, are established by the material’s band structure. The band structure defines the performance of semiconductor electronics, but it is fixed by the material’s crystal structure and chemical composition. The ability to tune its characteristics would allow enhanced functionality and flexibility of future electronic and optical devices. Recently, an electrically tunable band gap was realized in a crystal structure and chemical composition. The ability to realize via a hopping of electrons between localized states on the Mott energy gap, the electronic transport in SIO is most likely dominated by a small area near the contact (on the SIO side) for the electrical potential drop occurs essentially in the direct vicinity of the point contact on the SIO side, thus resulting in a locally high electric field E. Note that the so-called constriction resistance from a small area near the contact (on the SIO side) dominates the measured resistance over other resistive contributions, including those from the bulk of the crystal and the Cu tip and back electrodes. The latter can be considered as equipotential electrodes because of their relatively high conductivity (Cu vs SIO). When an electric bias is applied between the electrodes, the electrical potential drop occurs essentially in the direct vicinity of the point contact on the SIO side, thus resulting in a locally high electric field E as well as high local current densities ρ = E.

Our sample is a single crystal of Sr$_2$IrO$_4$ (1.5 mm × 1 mm × 0.5 mm) synthesized via a self-flux technique [12]. High electric fields were applied to the SIO crystal using nanoscale point contacts. The inset to Fig. 1(a) shows schematically a point contact between a sharpened Cu tip and the crystal. The tip is brought into contact with a (001) surface of the crystal with a standard mechanically controlled point-contact system described elsewhere [13]. The system provides a means to produce point contacts with sizes a [see inset to Fig. 1(a)] ranging from microns down to a few nanometers. An electrical current is injected through the contact into the crystal and flows (primarily) along the [001] c axis into a macroscopic Cu electrode on the back side of the crystal. From the so-called contact resistance from a small area near the contact (on the SIO side) dominates the measured resistance over other resistive contributions, including those from the bulk of the crystal and the Cu tip and back electrodes. The latter can be considered as equipotential electrodes because of their relatively high conductivity (Cu vs SIO). When an electric bias is applied between the electrodes, the electrical potential drop occurs essentially in the direct vicinity of the point contact on the SIO side, thus resulting in a locally high electric field E as well as high local current densities ρ = E.

Figure 1(a) shows current-voltage (I-V) characteristics of ten different point contacts with zero-bias resistances ranging from 13 to 27 kΩ measured at T = 77 K. Contact sizes a can be estimated from the measured contact resistance R using a simple model [13] for diffusive transport that gives $R = \rho/2a$, where ρ is the resistivity of SIO. Assuming $\rho \approx 50 \Omega \cdot cm$ at liquid nitrogen temperature [7], this analysis yields a ranging from 4.8 to 2.3 Ω for $R = 13–27 \Omega$. The local electric fields and current densities at the highest bias are of the order $E \sim 10^7 V/m$ and $j \sim 10^8 A/m^2$, respectively. All I-V curves show a similar nonlinear behavior: the contact resistance decreases with increasing dc bias as shown in Fig. 1(b); the decrease in contact resistance is symmetric at positive and negative biases. From now on we will mostly focus on such...
from a series of transport models/physical mechanisms most often applied to semiconductor junctions: (i) defect-induced traps in a semiconductor/insulator crystal are often associated with localized electron states within the band gap; the latter alter the crystal’s Fermi level and, therefore, its transport properties via so-called space charge limited currents, which are expected to lead to an $I \sim V^\alpha$ dependence [15], where $\alpha$ is a parameter (usually between 1 and 2) defined by details of defects/charge traps in the semiconductor [dark yellow trace in Fig. 1(d)] is for $\alpha = 2$; (ii) the emission of carriers from traps stimulated by an applied electric field can lead to Poole-Frenkel currents $j = j_0 e^{-\beta E V}$, where $j_0 = \alpha_0 E$ and $E$ is the electric field close to the contact [16]; such currents can become significant at high enough electric fields and lead to nonlinear characteristics as shown by green traces in Figs. 1(c) and 1(d), where the applied field is represented by either current or voltage; (iii) a tunneling barrier at the interface between the Cu tip and the SIO crystal can promote a decrease in the tunneling junction resistance with increasing bias due to an enhancement of the thermally excited transport across a biased junction [pink curve in Fig. 1(d)]; (iv) a simple Joule heating may lead to a decrease in the crystal’s resistivity at an elevated temperature, which can be modeled by the temperature dependence of resistivity $\rho \propto e^{A/k_B T}$ and the bias dependence of the temperature in the contact $T \propto V^2$ (or $\propto F^2$) [17] [cyan curves in Figs. 1(c) and 1(d)]. All models [(i)–(iv)] predict a decrease in the contact resistance $R$ with an increasing bias voltage $V$ consistent with our observations; however, systematic discrepancies between the measured and calculated resistance fail to provide a satisfactory fit of the $R(I)$ or $R(V)$ characteristic with any model parameters. It is thus obvious that none of the established physical mechanisms discussed above can provide an adequate agreement with our observations. Below we propose a new mechanism that is consistent with our observations [red trace in Fig. 1(c)] and may involve a change in the oxide’s electronic structure under externally applied electric fields via a field-induced lattice distortion.

### III. FIELD-EFFECT MODEL

Since electronic states in 5$d$ transition-metal oxides are extremely sensitive to the overlap of orbitals from neighboring crystal sites, even a subtle change of the lattice structure may lead to a considerable modification of the crystal’s electronic structure. For instance, lattice distortions induced in SIO by high pressure [18] and epitaxial strain [19] were found to change the effective correlated energy gap between 200 and 50 meV at liquid nitrogen temperature. Recent studies of the ferroelectric properties in SIO [20] have found that an applied electric field can induce an electric polarization; the latter may be associated with a field-driven displacement of oxygen anions in Ir-O-Ir bonds. In our experiments, extremely high local electric fields may be sufficient to alter the equilibrium positions of oxygen with respect to iridium ions and induce distortions of the corner shared IrO$_6$ octahedra, thus provoking modifications of the localized states and electronic structure. We have used an electrically tunable activation energy model to fit our data for the bias-dependent resistance. It was found that the data are well fitted in the entire range of applied bias.

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**FIG. 1.** (Color online) Current-voltage characteristics of SIO point contacts measured at $T = 77 \text{K}$. (a) Voltage ($V$) vs current ($I$) characteristics of 11 point contacts with zero-bias resistances ranging from 13 to 27 kΩ are shown in different colors. The inset shows schematically a point contact between a sharpened Cu tip (top light gray) and the crystal (dark gray) on a Cu back electrode (bottom light gray). (b) Resistance ($R = V/I$) vs current ($I$) plots for the same 11 point contacts. (c), (d) Analysis of $R$ vs $I$ (c) and $V$ (d); measured characteristics (black) are shown together with fits by different models: Joule heating (dashed cyan), Poole-Frenkel (dashed green), space charge limited currents (dashed dark yellow), tunneling barrier (dashed pink), and field-effect model (red).

**Notes:**
- The observed “S” shape of the $I$-$V$ curves is in good agreement with previous SIO studies of bulk crystals [9] and polycrystalline films [10].
- Unlike those standard bulk measurements, our point contacts provide a means to probe the electron transport on a local scale in SIO (~point-contact size $a$) subject to extremely high electric fields (~$10^7$ V/m).
- In what follows, we examine several established models for explaining the observed nonlinear $I$-$V$ behavior in undoped semiconductors/insulators, including impurities, defects/traps, and interfacial barriers. We will use both current and voltage as fitting parameters since (a) the local current density is expected to scale with the local electric field while (b) the applied voltage is traditionally used to estimate the applied fields in point contacts; but as the applied field spreads over a larger sample space, it may not reflect well on its local nature. Note that the nonlinear $I$-$V$ curves are symmetric in applied bias that rules out the Schottky barrier as a possible cause for the nonlinearity.
- Figures 1(c) and 1(d) show $R(I)$ and $R(V)$ data (black), respectively, for a representative point contact ($R = 17.5$ kΩ; $a \sim 3.5$ μm) together with fits (colored traces) originating...
currents \( I \) [red curve in Fig. 1(c)] with the following model:

\[
R(X) = A \ast e^{\Delta(I)/2k_BT}, \quad \Delta(I) = \Delta_0 - B \ast |I|
\]  

(1)

where \( \Delta_0 \) is the thermal activation energy at zero bias \( (I = 0) \) for a given temperature \( T \), and \( A \) and \( B \) are fitting parameters. Note that when using the applied voltage \( V \) instead of current \( I \) in Eq. (1), the fitting shows significant deviations from the observations [red curve in Fig. 1(c)], which indicates that the current is a better measure of the local electric field in a diffusive point contact. Equation (1) was successfully used to fit the data from contacts with different sizes/resistances (see Sec. V below). Our analysis suggests that the activation energy \( \Delta \) decreases by about 16% at the maximum applied field \( (at \ I = 3 \ mA \ in \ Fig. \ 1) \). These changes may originate from the field-driven lattice dynamics discussed in the next section, Sec. IV.

It should be noted that a model based on the VRH mechanism [21,22] of electronic conduction can also be used to fit our data for the bias-dependent resistance. In the presence of a strong electric field, carriers can gain energy when hopping along the field, which effectively increases the thermal energy available for hopping and can be taken into account by the VRH model as \( \rho = \rho_0 \exp[k_BT_0/(k_BT + e\epsilon Ed)]^{1/4} \), where \( T_0 \) is the characteristic temperature, \( e \) is the electron charge, \( \epsilon \) is relative dielectric constant, \( E \) is electric field, and \( d \) is the average hopping distance [22]. This model gives similarly good fits to our data (not shown), but it results in an unrealistically small hopping distance \( \sim 10^{-3} \ \text{Å} \). Together with recent studies [7,9,11] that find a thermally activated behavior in SIO at \( T \sim 100 \ \text{K} \) and above, this result suggests that the observed bias-dependent resistivity can be best described by an electrically tunable activation energy model [Eq. (1)] and demands further theoretical progress.

IV. LATTICE DYNAMICS

Since the band structure of SIO is closely associated with its crystalline structure and extremely sensitive to any variations in Ir-O bonds, it is possible that the observed variations of the activation energy originate from a lattice distortion driven by electric fields. Previous studies in SIO have shown that distortions of IrO\(_6\) octahedra can be induced by magnetic field [7], high pressure [18], or epitaxial strain [19]. Here we estimate the lattice distortions induced in SIO by an electric field applied in our experiments. The energy potential of each oxygen O\(_2^−\) ion in SIO can be approximately described by a simple harmonic oscillator model. In the presence of an external electric field \( E \), this simple model gives the energy profile as \( U = \frac{1}{2}kx^2 + eEx \), where \( x \) is the ion’s position, \( e \) the electron charge, \( E \) the applied field, and \( k \) is the spring constant of the ionic potential. In an applied field the equilibrium energy minimum is no longer at \( x = 0 \) but at \( x_{\text{min}} = eE/k \). The constant \( k \) in SIO can be estimated with the following arguments: it is known that \( k \sim 10^{-12} \ \text{eV Å}^{-2} \) in some 3d transition-metal (Fe, Co, Cr) oxides; in a 5d heavy metal oxide like SIO, it is expected to be smaller since the Ir-O bond is considerably weaker than that of O with 3d metal ions. If \( k \) is assumed to be \( \sim 1 \ \text{eV Å}^{-2} \) [one order of magnitude smaller than in 3d transition-metal oxides] and \( E \sim 20 \ \text{MV/m} \) like in our experiments (e.g., for a contact with \( R = 17.5 \ \text{kΩ} \) and \( a = 3.6 \ \text{µm} \)), we estimate the displacement \( x_{\text{min}} \) of oxygen ions to be \( \sim 2 \times 10^{-3} \ \text{Å} \) (\( \sim 0.1\% \) of the Ir-O bond length). The displacements are expected to be along the applied field \( E \), i.e., along the \( c \) axis (perpendicular to the basal plane). Figure 2 illustrates the associated changes of IrO\(_6\) octahedra. The four Ir-O bonds in the basal plane [see Fig. 2(b) at \( E = 0 \)] are elongated in a similar fashion [see Fig. 2(c) at \( E \neq 0 \)]. The two apical Ir-O bonds experience opposite effects on the bond length—one increases and the other decreases.

Assuming a zero effect of the apical bonds on the activation energy due to their mutual compensation, our model suggests that an applied electric field favors buckled basal planes with longer Ir-O bonds. These distortions normally reduce the bandwidth and increase the band gap since the overlap integral \( b \) is proportional to \( \cos^2(\omega/2)/d^{3.5} \), where \( \omega \) is the M-O-M bond angle and \( d \) is the M-O bond length in oxides with the perovskite or perovskite-related structures [23]. Our observations indicate that the activation energy decreases as the structure becomes more distorted under the electric field in SIO, which is just opposite to the relationship between the structural distortion and the activation energy found in 3d oxides [24]. This may be due to a particular sensitivity of our measurements to the electronic transport along the \( c \) axis which is largely controlled by the Sr\(_2\)O\(_2\) rock-salt layer while the distortions in the IrO\(_2\) basal plane have a smaller effect. In
comparison, an increased activation energy has been reported for SIO under epitaxial strain [19], or under high pressure [18].

From our temperature-dependent measurements (see Sec. VI), we have defined the activation energy decrease of about 8 meV under 20 MV/m (around liquid nitrogen temperature), which corresponds to a change of $\sim 15\%$ from the gap $\Delta_0 = 55$ meV at zero bias. These estimations of the electric-field effect agree well with the effects of high pressure [18] and epitaxial strain [19] on the electronic properties of SIO which give $\sim 10\%$ reduction in the measured activation energy when the lattice constant changes by $\sim 0.1$–1%.

V. UNIVERSAL $E$ DEPENDENCE

Figure 1 shows current-voltage characteristics of SIO point contacts with different sizes (from 2.3 to 4.8 $\mu$m). Electric fields produced in a contact by an applied electrical bias depend on the contact size $a$—in smaller contacts the fields are higher at the same bias. The maximum field produced in the contact subject to an electric current $I$ (current density $j$) can be estimated from $E = j/\sigma = I/\sigma A$, where $\sigma$ is conductivity and $A = \pi a^2/4$ is cross-sectional area of the contact. Following the field-effect model introduced in Sec. III, we can express the contact resistance $R$ as a function of electric field $R(E) \sim \exp[(\Delta_0 - b|E|)/2k_B T]$ with $\beta = B(I/E)$. Figure 3 shows the normalized contact resistance $[R(E) - R(E = 0)]/R(E = 0)$ as a function of applied electric field for point contacts with different size (different colors correspond to different contacts from Fig. 1). The field-effect model suggests that all curves would collapse on a universal $R(E)$ dependence. Our data for different contacts fall within an envelope between two boundary curves (dashed gray in Fig. 3) predicted by the field-effect model with the parameter $\beta$ varied by 10%. Given an uncertainty in the contact geometry and spatial nonuniformity of the electric field, we find such behavior to be in good agreement with the proposed field-effect model. Our data from different contacts show that the contact resistance drops by approximately 50% in electric fields of about 20–30 MV/m and suggest a similar variation of the activation energy.

VI. $T$-DEPENDENT MEASUREMENTS

We verified our field-dependent activation energy model [Eq. (1)] by measuring the temperature dependence of the $I$-$V$ curves. Figure 4(a) shows $R(I)$ data (black symbols) measured at temperatures $T$ from 83–166 K. The $R(I)$ data at different temperatures were fitted by Eq. (1) (red curves). Figures 4(b)–4(d) show temperature dependencies of the three fitting parameters $A$, $\Delta_0$, and $B$, respectively. The parameter $A$ is related to intrinsic properties of the material which, in principle, may vary slowly with temperature. The values of $\Delta_0$—the activation energy at zero bias—agree well with the ones extracted from the ln($R$) vs $1/T$ data (shown later), and the increase of $\Delta_0$ with increasing temperature is also consistent with previous results in SIO [7,18,19]. Finally, the third fitting parameter $B$, which quantifies the magnitude of the field effects, is found to decrease with increasing temperature since at higher $T$ the same range of applied currents $I$ results in a smaller range of applied electric fields due to an increased conductivity of SIO.

Variations of the activation energy as a function of temperature and electrical bias can be probed directly with standard temperature-dependent resistivity (contact resistance) measurements at different biases. Figure 5(a) shows the zero-bias resistance $R$ vs $T$ along with the ln($R$) vs $1/T$ plot (inset to Fig. 3(a)) of the same data. The slope of the latter dependence is expected to give the value of $\Delta$. Following this standard approach we have extracted the temperature dependence of the zero-bias activation energy $\Delta_0$ [Fig. 5(b)] from the derivative $d[\ln(R_0)]/d(1/T)$ of the data in the inset to Fig. 4(a). It is found that our extrapolated values of $\Delta_0$($\sim 100$ meV) [Fig. 5(b)]
agree well with the correlated energy gap characterized by optical methods [5] within the investigated temperature range, implying a good correlation between the transport-measured thermal activation energy and the intrinsic correlated energy gap. By performing a similar analysis at different values of the applied bias current, one can extract the bias dependence of $\Delta$ at a fixed temperature. The result of such an analysis at $T = 167$ K shows [Fig. 5(c)] that $\Delta$ decreases (from its zero-bias value $\Delta_0$) with increasing bias $I$, in agreement with the proposed field-effect model.

VII. SWITCHING

In addition to the continuous variations of the resistance as a function of the applied bias, we have observed a reproducible and reversible resistive switching. One can notice small jumps in $I$-$V$ characteristics of different point contacts in Fig. 1. Figure 6(a) shows an example of such a behavior. Here the black curve shows the $R(I)$ sweep from positive to negative biases and the gray curve shows the sweep back. When the applied bias current increases beyond a critical $|I_c|$ value the contact resistance has a step decrease. Following the scenario of the field-effect model, the step decrease may be associated with a field-induced structural transition between two metastable states. The ions being displaced/migrated under high electric fields may encounter potential barriers that need a certain energy to be overcome; the applied electric field modifies the energy landscape and, at a certain critical electric field $E_c$ (critical $I_c$), could promote the transition over such a barrier, i.e., switching. We can estimate the variation of $\Delta$ between the two states (below and above $I_c$) from the corresponding decrease in resistance. For instance, the switching shown in Fig. 4(a) gives a change of $\Delta$ about 0.34 meV. Furthermore, the switching threshold $I_c$ exhibits a clear magnetic field dependence $I_c(\mu_0H)$, which correlates with the point-contact $R(\mu_0H)$ magnetoresistance [13] observed at zero bias [compare Figs. 6(b) and 6(c)]. The increase in $I_c(\mu_0H)$ with increasing field correlates with the decrease in $R(\mu_0H)$, but their relative changes are quite different and cannot be explained by a field-independent critical voltage $V_c = I_cR$. Previous studies suggested that lattice distortions in SIO may cause a magnetoresistive effect due to a strong spin-orbit coupling [7,8,14]. The correlations between the magnetoresistance and resistive switching observed in our present work suggest that the magnetoresistive phenomenon in SIO could originate from the band structure modifications associated with the field-induced lattice distortions.

In what follows we estimate and compare electric fields needed for the resistive switching observed in contacts with different size. Figure 6(d) shows how the measured $E_c$ depends on the contact size $a$. We find the strength of the critical field $E_c$ to be independent of the bias polarity [compare open and solid symbols in Fig. 6(d)] and fall within a range from 6 to 10 MV/m. It can be noticed that $E_c$ has a tendency to decrease slightly with increasing contact size [dashed red line in Fig. 6(d)]. The latter may be associated with an increased number of oxygen ions subject to high electric fields in larger contacts.
VIII. CONCLUSION

We have studied the effects of high electric fields on transport properties of the antiferromagnetic Mott insulator Sr$_2$IrO$_4$. Using point-contact technique, we applied electric fields up to a few MV/m to a single crystal of Sr$_2$IrO$_4$ and measured its current-voltage characteristics at different temperatures from 77 to 300 K. A continuous reduction in the material’s resistivity has been observed as a function of increasing electric bias, which can be characterized by a reduction in the transport activation energy by as much as 16%. Temperature-dependent resistivity measurements provide a means to unambiguously retrieve the bias dependence of the activation energy from the Arrhenius plots at different biases. We also demonstrated the feasibility of reversible resistive switching induced by the electric bias at a threshold current, which exhibits a clear magnetic field dependence and correlates with the material’s magnetoresistance. Such a combined effect of electric and magnetic fields on the conductivity of Sr$_2$IrO$_4$ demonstrate the potential of electrical means for tuning electronic properties in 5$d$ transition-metal oxides and suggests a promising path towards development of functional devices, e.g., in the emerging field of antiferromagnetic spintronics.

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